Fabrizio Arciprete

List of Publications by Year
in descending order

95 papers	1,456 citations	304743 22 h-index	361022 35 g-index
96 all docs	96 docs citations	96 times ranked	1408 citing authors

#	Article	IF	Citations
1	Metal - Insulator Transition Driven by Vacancy Ordering in GeSbTe Phase Change Materials. Scientific Reports, 2016, 6, 23843.	3.3	93
2	Facile synthesis of graphene-phthalocyanine composites as oxygen reduction electrocatalysts in microbial fuel cells. Applied Catalysis B: Environmental, 2018, 237, 699-707.	20.2	89
3	Graphene oxide nanoplatforms to enhance catalytic performance of iron phthalocyanine for oxygen reduction reaction in bioelectrochemical systems. Journal of Power Sources, 2017, 356, 381-388.	7.8	75
4	Tracing the two- to three-dimensional transition in the InAs/GaAs(001) heteroepitaxial growth. Physical Review B, 2003, 67, .	3.2	69
5	MnOx-based electrocatalysts for enhanced oxygen reduction in microbial fuel cell air cathodes. Journal of Power Sources, 2018, 390, 45-53.	7.8	64
6	Step erosion during nucleation of InAsâˆ•GaAs(001) quantum dots. Applied Physics Letters, 2005, 86, 241913.	3.3	50
7	Apparent critical thickness versus temperature for InAs quantum dot growth on GaAs(001). Applied Physics Letters, 2006, 88, 161903.	3.3	49
8	Far-Infrared and Raman Spectroscopy Investigation of Phonon Modes in Amorphous and Crystalline Epitaxial GeTe-Sb2Te3 Alloys. Scientific Reports, 2016, 6, 28560.	3.3	45
9	Kinetic aspects of the morphology of self-assembled InAs quantum dots on GaAs(001). Applied Physics Letters, 2001, 78, 320-322.	3.3	40
10	Chemical and structural arrangement of the trigonal phase in GeSbTe thin films. Nanotechnology, 2017, 28, 065706.	2.6	39
11	How kinetics drives the two- to three-dimensional transition in semiconductor strained heterostructures: The case of InAsâˆ•GaAs(001). Applied Physics Letters, 2006, 89, 041904.	3.3	37
12	Infrared surface absorption inSi(111)2Ã—1observed with reflectance anisotropy spectroscopy. Physical Review B, 2002, 66, .	3.2	33
13	Temperature dependence of the size distribution function of InAs quantum dots on GaAs(001). Physical Review B, 2010, 81, .	3.2	32
14	Electrical transport properties of artificially layered films of [BaCuO2]2/[(Sr,Ca)CuO2]n. Applied Physics Letters, 1997, 71, 959-961.	3.3	31
15	Self-assembly of InAs and Si/Ge quantum dots on structured surfaces. Journal of Physics Condensed Matter, 2004, 16, S1503-S1534.	1.8	31
16	InAs/GaAs(001) epitaxy: kinetic effects in the two-dimensional to three-dimensional transition. Journal of Physics Condensed Matter, 2007, 19, 225006.	1.8	31
17	Morphological instabilities of the InAs/GaAs(001) interface and their effect on the self-assembling of InAs quantum-dot arrays. Applied Physics Letters, 2002, 81, 2270-2272.	3.3	29
18	Sudden nucleation versus scale invariance of InAs quantum dots on GaAs. Physical Review B, 2007, 75, .	3.2	29

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19	Reflection high energy electron diffraction observation of surface mass transport at the two- to three-dimensional growth transition of InAs on GaAs(001). Applied Physics Letters, 2005, 87, 252101.	3.3	27
20	Graphene Oxide Oxygen Content Affects Physical and Biological Properties of Scaffolds Based on Chitosan/Graphene Oxide Conjugates. Materials, 2019, 12, 1142.	2.9	26
21	Analysis of InAs(001) surfaces by reflectance anisotropy spectroscopy. Physical Review B, 2001, 64, .	3.2	25
22	Interplay between Structural and Thermoelectric Properties in Epitaxial Sb₂₊<i>_x</i>Te₃ Alloys. Advanced Functional Materials, 2019, 29, 1805184.	14.9	25
23	Influence of surface crystal-orientation on transfer doping of V2O5/H-terminated diamond. Applied Physics Letters, 2018, 112, 181602.	3.3	23
24	Surface versus bulk contributions from reflectance anisotropy and electron energy loss spectra of theGaAs(001)â^’c(4Ã—4)surface. Physical Review B, 2003, 68, .	3.2	22
25	Annealing effects on faceting of InAsâ^•GaAs(001) quantum dots. Applied Physics Letters, 2009, 94, 021901.	3.3	21
26	Modulation of van der Waals and classical epitaxy induced by strain at the Si step edges in GeSbTe alloys. Scientific Reports, 2017, 7, 1466.	3.3	21
27	Surface states at theGaAs(001)2Ã—4surface. Physical Review B, 2004, 69, .	3.2	19
28	EXAFS study of the [BaCuO2]2/[(Ca,Sr)CuO2]n artificial superconducting superlattices. Physica C: Superconductivity and Its Applications, 2000, 334, 64-76.	1.2	18
29	Role of interfaces on the stability and electrical properties of Ge2Sb2Te5 crystalline structures. Scientific Reports, 2017, 7, 2616.	3.3	15
30	The Unexpected Role of Arsenic in Driving the Selective Growth of InAs Quantum Dots on GaAs. ACS Nano, 2013, 7, 3868-3875.	14.6	14
31	Tailoring active sites of iron-nitrogen-carbon catalysts for oxygen reduction in alkaline environment: Effect of nitrogen-based organic precursor and pyrolysis atmosphere. Electrochimica Acta, 2021, 391, 138899.	5.2	14
32	Observation of interface states by high-resolution electron-energy-loss spectroscopy in metal-GaAs(110) junctions. Physical Review B, 1996, 53, 12948-12955.	3.2	13
33	The GaAs()-c(4Ã—4) surface: a new perspective from energy loss spectra. Surface Science, 2003, 524, L71-L76.	1.9	12
34	Manipulating surface diffusion and elastic interactions to obtain quantum dot multilayer arrangements over different length scales. Applied Physics Letters, 2014, 105, .	3.3	12
35	Keep it simple and switch to pure tellurium. Science, 2021, 374, 1321-1322.	12.6	12
36	Valence band and In-4d core level photoemission study of de-capped and ion-bombarded-annealed InAs(001) epitaxial surfaces. Surface Science, 2005, 576, 123-130.	1.9	11

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37	In situ X-ray absorption measurements of the Cu/MgO() interface. Surface Science, 2002, 512, L341-L345.	1.9	10
38	Single quantum dot emission by nanoscale selective growth of InAs on GaAs: A bottom-up approach. Applied Physics Letters, 2008, 93, 231904.	3.3	10
39	Complex domain-wall dynamics in compressively strained<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Ga</mml:mtext></mml:mrow><mml:mrow><mml:mn>1</mml: Physical Review B, 2008, 78, .	3.2	10
40	Coarsening effect on island-size scaling: The model case InAs/GaAs(001). Physical Review E, 2012, 86, 061605.	2.1	10
41	Tailoring morphology and structure of manganese oxide nanomaterials to enhance oxygen reduction in microbial fuel cells. Synthetic Metals, 2020, 268, 116487.	3.9	10
42	Reactivity of the Bi2Sr2CaCu2O8 and Bi1.7Pb0.3Sr2CaCu2O8 surfaces for d-metal overlayers. Physica C: Superconductivity and Its Applications, 1992, 196, 79-89.	1.2	9
43	Anisotropy of the GaAs(001)-Î²2(2Ã—4) surface from high-resolution electron energy loss spectroscopy. Physical Review B, 2003, 67, .	3.2	9
44	Kinetically driven selective growth of InAs quantum dots on GaAs. Journal of Materials Research, 2013, 28, 3201-3209.	2.6	9
45	Designing epitaxial GeSbTe alloys by tuning the phase, the composition, and the vacancy ordering. Journal of Applied Physics, 2018, 123, .	2.5	9
46	Increasing Optical Efficiency in the Telecommunication Bands of Strain-Engineered Ga(As,Bi) Alloys. Physical Review Applied, 2020, 14, .	3.8	9
47	Dynamic behavior of silver islands growing on GaAs(001)2Ã—4 substrate. Surface Science, 2000, 445, L17-L22.	1.9	8
48	Sum rules in surface differential reflectivity and reflectance anisotropy spectroscopies. Applied Surface Science, 2001, 175-176, 777-782.	6.1	8
49	InxGa(1â^'x)As quantum dots grown on GaAs studied by EXAFS in total reflection mode (ReflEXAFS). Nuclear Instruments & Methods in Physics Research B, 2003, 200, 85-89.	1.4	8
50	Optical anisotropy of oxidized InAs() surfaces. Surface Science, 2002, 515, 281-286.	1.9	7
51	Adsorption of molecular oxygen on GaAs(001) studied using high-resolution electron energy-loss spectroscopy. Physical Review B, 2006, 73, .	3.2	7
52	Temperature-dependent NÃ©el wall dynamics in GaMnAs/GaAs. New Journal of Physics, 2010, 12, 093022.	2.9	7
53	Interface formation between d metals and the Bi2Sr2CaCu2O8 surface. Physica C: Superconductivity and Its Applications, 1991, 180, 101-107.	1.2	6
54	AIRFLY: Measurement of the Air Fluorescence Radiation Induced by Electrons. Nuclear Physics, Section B, Proceedings Supplements, 2006, 150, 186-189.	0.4	6

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55	AIRFLY: Measurement of the uorescence yield in atmospheric gases. European Physical Journal D, 2006, 56, A361-A367.	0.4	6
56	Comparative study of low temperature growth of InAs and InMnAs quantum dots. Nanotechnology, 2011, 22, 195602.	2.6	6
57	The role of kinetics on the Mn-induced reconstructions of the GaAs(001) surface. Journal of Applied Physics, 2011, 109, .	2.5	6
58	Scaling behavior of GaAs and GaMnAs quantum rings grown by droplet epitaxy. Applied Physics Letters, 2012, 101, 141901.	3.3	6
59	Hints for a General Understanding of the Epitaxial Rules for van der Waals Epitaxy from Geâ€Sbâ€Te Alloys. Advanced Materials Interfaces, 2022, 9, .	3.7	6
60	Growth, Electronic and Electrical Characterization of Ge-Rich Geâ€“Sbâ€“Te Alloy. Nanomaterials, 2022, 12, 1340.	4.1	6
61	Comparative study of Ag growth on GaAs(001) and (110) surfaces. Surface Science, 1998, 419, 24-28.	1.9	5
62	Crystallization Study of Geâ€Rich (GeTe)<i>_m</i>(Sb₂Te₃)<i>_n</i> Using Twoâ€Step Annealing Process. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800632.	2.4	5
63	Electronic properties of GaAsBi(001) alloys at low Bi content. Physical Review Materials, 2019, 3, .	2.4	5
64	Reflectance anisotropy spectroscopy of strain-engineered GaAsBi alloys. Applied Physics Letters, 2022, 120, .	3.3	5
65	Electronic structure of the GaAs(001)2Ã—4 and GaAs(110) surfaces studied by high-resolution electron-energy-loss spectroscopy. Physical Review B, 1998, 58, R10139-R10142.	3.2	4
66	XPS and STM study of Mn incorporation on the GaAs(001) surface. Superlattices and Microstructures, 2009, 46, 258-265.	3.1	4
67	In-line correlation and ordering of InAs/GaAs multistacked Quantum Dots structures. Journal of Crystal Growth, 2015, 419, 138-142.	1.5	4
68	Interface Formation during the Growth of Phase Change Material Heterostructures Based on Ge-Rich Ge-Sb-Te Alloys. Nanomaterials, 2022, 12, 1007.	4.1	4
69	Structural and Electrical Properties of Annealed Ge2Sb2Te5 Films Grown on Flexible Polyimide. Nanomaterials, 2022, 12, 2001.	4.1	4
70	Selective growth of InAs quantum dots on SiO₂-masked GaAs. Journal of Nanophotonics, 2009, 3, 031995.	1.0	3
71	Single QD emission from arrays of QD chains obtained by patterning-free method. International Journal of Higher Education Management, 2015, 1, 33-37.	1.3	3
72	Stress-determined nucleation sites above GaAs-capped arrays of InAs quantum dots. Journal of Applied Physics, 2016, 120, 125704.	2.5	3

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73	The InAs/GaAs(001) Quantum Dots Transition: Advances on Understanding. , 2008, , 1-23.		3
74	InAs Epitaxy on GaAs(001): A Model Case of Strain-Driven Self-assembling of Quantum Dots. , 2012, , 73-125.		3
75	Epitaxial growth of GeTe/Sb2Te3 superlattices. Materials Science in Semiconductor Processing, 2022, 137, 106244.	4.0	3
76	Magnetic aftereffect in compressively strained GaMnAs studied using Kerr microscopy. Physical Review B, 2010, 81, .	3.2	2
77	EELPS investigation of YBa-2Cu3O7-Î´ thin films and sintered samples. Physica C: Superconductivity and Its Applications, 1991, 180, 132-135.	1.2	1
78	Angular dependence of the oxygen K-edge fine structure in electron-energy loss spectra of Bi2âˆ'xPbxSr2CaCu2O8. Physica C: Superconductivity and Its Applications, 1993, 218, 301-308.	1.2	1
79	Magnetoelectric properties of oxygenated (Ga,Mn)As. Physical Review B, 2011, 83, .	3.2	1
80	Magnetism and carrier modulation in (Ga,Mn)As/organic-dye hybrid devices. Applied Physics Letters, 2011, 98, 022503.	3.3	1
81	Selective growth of InAs quantum dots on GaAs driven by as kinetics. Crystal Research and Technology, 2014, 49, 546-551.	1.3	1
82	Anisotropic cation diffusion in the GaAs capping of InAs/GaAs(001) quantum dots. Journal of Applied Physics, 2016, 120, 235303.	2.5	1
83	2D Voronoi tessellation generated by lines and belts of dots. Physics Letters, Section A: General, Atomic and Solid State Physics, 2016, 380, 516-519.	2.1	1
84	Tuning the growth for a selective nucleation of chains of Quantum Dots behaving as single photon emitters. Journal of Crystal Growth, 2017, 457, 177-183.	1.5	1
85	Two-dimensional antiferromagnetic ordering of the Mn/GaAs(001) interface. Physical Review B, 2019, 99, .	3.2	1
86	Disordering process of GeSb₂Te₄ induced by ion irradiation. Journal Physics D: Applied Physics, 2020, 53, 134001.	2.8	1
87	A Special Section on Effects of Strain in Semiconductor Heterostructures. Nanoscience and Nanotechnology Letters, 2017, 9, 1064-1065.	0.4	1
88	Electron energy loss study of Ag- and Auî—¸GaAs(110) interfaces. Journal of Electron Spectroscopy and Related Phenomena, 1995, 76, 449-454.	1.7	0
89	XAS STUDY OF (BaCuO2)2/(CaCuO2)n SUPERLATTICES. International Journal of Modern Physics B, 2000, 14, 2628-2633.	2.0	0
90	Morphology of Self-Assembled InAs Quantum Dots on GaAs(001). Materials Research Society Symposia Proceedings, 2001, 696, 1.	0.1	0

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91	Morphology of Self-Assembled InAs Quantum Dots on GaAs(001).. Materials Research Society Symposia Proceedings, 2001, 707, 671.	0.1	0
92	Structural study of the InAs quantum-dot nucleation on GaAs(001). Microelectronics Journal, 2003, 34, 419-422.	2.0	0
93	Electronic anisotropy of the GaAs(001) surface studied by energy loss spectroscopy. Microelectronics Journal, 2003, 34, 595-597.	2.0	0
94	The Influence of the Wetting Layer Morphology on the Nucleation and the Evolution of InAs/GaAs (001) Quantum Dots. Semiconductor Conference, 2009 CAS 2009 International, 2007, , .	0.0	0
95	Role of As in the Anisotropic Positioning of Self-Assembled InAs Quantum Dots. Materials Research Society Symposia Proceedings, 2013, 1551, 3-9.	0.1	0